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Day : Sunday
 Date: 7/11/2004
 Time: 18:51:51

Inventor Name Search Result

Your Search was:

Last Name = KINZER

First Name = DANIEL M

Application#	Patent#	Status	Date Filed	Title	Inventor Name 51
<u>60104148</u>	Not Issued	159	10/14/1998	MOSGATED DEVICE WITH TRENCH STRUCTURE AND REMOTE CONTACT AND PROCESS FOR ITS MANUFACTURE	KINZER , DANIEL M.
<u>60082803</u>	Not Issued	159	04/23/1998	NEW P-CHANNEL TRENCH MOSFET STRUCTURE	KINZER , DANIEL M.
<u>60031051</u>	Not Issued	159	11/18/1996	PROCESS FOR MANUFACTURE OF A P-CHANNEL MOS GATED DEVICE WITH BASE IMPLANT THROUGH THE CONTACT WINDOW	KINZER , DANIEL M.
<u>60029491</u>	Not Issued	159	10/25/1996	PROCESS FOR MANUFACTURE OF MOS GATED DEVICE WITH SELF ALIGNED CELLS	KINZER , DANIEL M.
<u>60029483</u>	Not Issued	159	10/24/1996	COMMONLY HOUSED DIVERSED SEMICONDUCTOR DIE	KINZER , DANIEL M.
<u>60013761</u>	Not Issued	159	03/20/1996	AMORPHOUS SILICON COMBINED WITH RESURF REGION FOR TERMINATION FOR MOSGATED DEVICE	KINZER , DANIEL M.
<u>60006688</u>	Not Issued	159	11/14/1995	TERMINATION STRUCTURE FOR SEMICONDUCTOR DEVICES AND PROCESS FOR MANUFACTURE THEREOF	KINZER , DANIEL M.
<u>60005076</u>	Not Issued	159	10/11/1995	TERMINATION STRUCTURE FOR SEMICONDUCTOR DEVICES AND PROCESS FOR MANUFACTURE THEREOF	KINZER , DANIEL M.
<u>09416796</u>	<u>6476443</u>	150	10/13/1999	MOSGATED DEVICE WITH TRENCH STRUCTURE AND	KINZER , DANIEL M.

				REMOTE CONTACT AND PROCESS FOR ITS MANUFACTURE	
<u>09292186</u>	Not Issued	124	04/15/1999	P-CHANNEL TRENCH MOSFET STRUCTURE	KINZER , DANIEL M.
<u>09225254</u>	<u>6410989</u>	150	01/04/1999	CHIP-SCALE PACKAGE	KINZER , DANIEL M.
<u>09197939</u>	<u>6144067</u>	150	11/23/1998	STRIP GATE POLY STRUCTURE FOR INCREASED CHANNEL WIDTH AND REDUCED GATE RESISTANCE	KINZER , DANIEL M.
<u>09193507</u>	<u>6207974</u>	150	11/17/1998	PROCESS FOR MANUFACTURE OF A P- CHANNEL MOS GATED DEVICE WITH BASE IMPLANT THROUGH THE CONTACT WINDOW	KINZER , DANIEL M.
<u>09185110</u>	<u>6194741</u>	150	11/03/1998	MOSGATED TRENCH TYPE POWER SEMICONDUCTOR WITH SILICON CARBIDE SUBSTRATE AND INCREASED GATE BREAKDOWN VOLTAGE AND REDUCED ON-RESISTANCE	KINZER , DANIEL M.
<u>09165541</u>	<u>6133616</u>	150	10/02/1998	TEMPSENSE FET WITH IMPLANTED LINE OF DIODES (EPS)	KINZER , DANIEL M.
<u>09095349</u>	<u>6180981</u>	150	06/09/1998	TERMINATION STRUCTURE FOR SEMICONDUCTOR DEVICES AND PROCESS FOR MANUFACTURE THEREOF	KINZER , DANIEL M.
<u>08956062</u>	<u>6043126</u>	150	10/22/1997	PROCESS FOR MANUFACTURE OF MOS GATED DEVICE WITH SELF ALIGNED CELLS	KINZER , DANIEL M.
<u>08946984</u>	<u>5879968</u>	150	10/08/1997	PROCESS FOR MANUFACTURE OF A P-CHANNEL MOS GATED DEVICE WITH BASE IMPLANT THROUGH THE CONTACT WINDOW	KINZER , DANIEL M.
<u>08822398</u>	<u>6100572</u>	150	03/20/1997	AMORPHOUS SILICON COMBINED WITH RESURF REGION FOR TERMINATION FOR MOSGATED DEVICE	KINZER , DANIEL M.

<u>08816829</u>	<u>5814884</u>	150	03/18/1997	COMMONLY HOUSED DIVERSE SEMICONDUCTOR DIE	KINZER , DANIEL M.
<u>08815814</u>	<u>6242800</u>	150	03/12/1997	HEAT DISSIPATING DEVICE PACKAGE	KINZER , DANIEL M.
<u>08784418</u>	<u>5808345</u>	150	01/16/1997	HIGH SPEED IGBT	KINZER , DANIEL M.
<u>08782568</u>	<u>5886383</u>	150	01/10/1997	INTEGRATED SCHOTTKY DIODE AND MOSGATED DEVICE	KINZER , DANIEL M.
<u>08727142</u>	<u>5731604</u>	150	10/08/1996	SEMICONDUCTOR DEVICE MOS GATED	KINZER , DANIEL M.
<u>08725566</u>	<u>5940721</u>	150	10/03/1996	TERMINATION STRUCTURE FOR SEMICONDUCTOR DEVICES AND PROCESS FOR MANUFACTURE THEREOF	KINZER , DANIEL M.
<u>08674982</u>	<u>5644148</u>	150	07/03/1996	POWER TRANSISTOR DEVICE HAVING ULTRA DEEP INCREASED CONCENTRATION REGION	KINZER , DANIEL M.
<u>08564917</u>	<u>5786619</u>	150	11/30/1995	DEPLETION MODE POWER MOSFET WITH REFRACTORY GATE AND METHOD OF MAKING SAME	KINZER , DANIEL M.
<u>08516683</u>	<u>5625226</u>	150	08/18/1995	SURFACE MOUNT PACKAGE WITH IMPROVED HEAT TRANSFER	KINZER , DANIEL M.
<u>08461509</u>	Not Issued	166	06/05/1995	POWER TRANSISTOR DEVICE HAVING ULTRA DEEP INCREASED CONCENTRATION REGION	KINZER , DANIEL M.
<u>08409347</u>	<u>5557127</u>	150	03/23/1995	TERMINATION STRUCTURE FOR MOSGATED DEVICE WITH REDUCED MASK COUNT AND PROCESS FOR ITS MANUFACTURE	KINZER , DANIEL M.
<u>08409181</u>	<u>5595918</u>	150	03/23/1995	PROCESS FOR MANUFACTURE OF P CHANNEL MOS-GATED DEVICE	KINZER , DANIEL M.
<u>08390099</u>	<u>5474946</u>	250	02/17/1995	REDUCED MASK PROCESS FOR MANUFACTURE OF MOS GATED DEVICES	KINZER , DANIEL M.
<u>08364514</u>	Not Issued	166	12/27/1994	POWER TRANSISTOR DEVICE HAVING ULTRA DEEP INCREASED CONCENTRATION REGION	KINZER , DANIEL M.

<u>08299533</u>	<u>5795793</u>	150	09/01/1994	PROCESS FOR MANUFACTURE OF MOS GATED DEVICE WITH REDUCED MASK COUNT	KINZER , DANIEL M.
<u>08288585</u>	<u>5475252</u>	150	08/10/1994	PROCESS FOR MANUFACTURE OF RADIATION RESISTANT POWER MOSFET AND RADIATION RESISTANT POWER MOSFET	KINZER , DANIEL M.
<u>08176672</u>	Not Issued	161	01/03/1994	SEMICONDUCTOR DEVICE WITH VERTICAL CONDUCTION POWER SECTION ISOLATED FROM CONTROL SECTIONS SECTIONS	KINZER , DANIEL M.
<u>07945106</u>	Not Issued	166	09/15/1992	POWER TRANSISTOR DEVICE HAVING ULTRA DEEP INCREASED CONCENTRATION REGION	KINZER , DANIEL M.
<u>07935829</u>	Not Issued	166	08/26/1992	SEMICONDUCTOR DEVICE WITH VERTICAL CONDUCTION IN A POWER SECTION AND A METHOD FOR PREPARING THE DEVICE	KINZER , DANIEL M.
<u>07779140</u>	Not Issued	161	10/18/1991	CIRCUIT FOR PROVIDING DV/DT IMMUNITY	KINZER , DANIEL M.
<u>07528145</u>	Not Issued	166	05/24/1990	CIRCUIT FOR PROVIDING DV/DT IMMUNITY	KINZER , DANIEL M.
<u>07399345</u>	<u>4974059</u>	150	08/28/1989	SEMICONDUCTOR HIGH-POWER MOSFET DEVICE	KINZER , DANIEL M.
<u>07391487</u>	<u>5023678</u>	150	08/09/1989	HIGH POWER MOSFET AND INTEGRATED CONTROL CIRCUIT THEREFOR FOR HIGH- SIDE SWITCH APPLICATION	KINZER , DANIEL M.
<u>07255111</u>	<u>4888504</u>	150	10/07/1988	BIDIRECTIONAL MOSFET SWITCHING CIRCUIT WITH SINGLE GATE BIAS	KINZER , DANIEL M.
<u>07160172</u>	<u>5472888</u>	150	02/25/1988	DEPLETION MODE POWER MOSFET WITH REFRACTORY GATE AND METHOD OF MAKING SAME	KINZER , DANIEL M.
<u>07054627</u>	<u>4866495</u>	150	05/27/1987	HIGH POWER MOSFET AND INTEGRATED CONTROL	KINZER , DANIEL M.

				CIRCUIT THEREFOR FOR HIGH-SIDE SWITCH APPLICATION	
<u>07048991</u>	Not Issued	166	04/29/1987	STRUCTURE AND METHOD OF MANUFACTURE OF HIGH POWER MOSFET DEVICE	KINZER , DANIEL M.
<u>07001629</u>	<u>5338693</u>	150	01/08/1987	PROCESS FOR MANUFACTURE OF RADIATION RESISTANT POWER MOSFET AND RADIATION RESISTANT POWER MOSFET	KINZER , DANIEL M.
<u>06878196</u>	<u>4721986</u>	150	06/25/1986	BIDIRECTIONAL OUTPUT SEMICONDUCTOR FIELD EFFECT TRANSISTOR AND METHOD FOR ITS MANUFACTURE	KINZER , DANIEL M.
<u>06755858</u>	<u>4755697</u>	150	07/17/1985	BIDIRECTIONAL OUTPUT SEMICONDUCTOR FIELD EFFECT TRANSISTOR	KINZER , DANIEL M.
<u>06581785</u>	Not Issued	161	02/21/1984	BIDIRECTIONAL OUTPUT SEMICONDUCTOR FIELD EFFECT TRANSISTOR AND METHOD FOR ITS MANUFACTURE	KINZER , DANIEL M.
<u>06573305</u>	Not Issued	166	01/23/1984	PHOTOVOLTAIC ISOLATOR AND PROCESS OF MANUFACTURE THEREOF	KINZER , DANIEL M.

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Inventor Name Search Result

Your Search was:

Last Name = KINZER

First Name = DANIEL M

Application#	Patent#	Status	Date Filed	Title	Inventor Name 11
<u>60159156</u>	Not Issued	159	10/13/1999	THREE COMMONLY HOUSED DIVERSE SEMICONDUCTOR DICE	KINZER , DANIEL M.
<u>60157740</u>	Not Issued	159	10/05/1999	TRENCH MOSFET WITH INTEGRATED SCHOTTKY DEVICE AND PROCESS FOR ITS MANUFACTURE	KINZER , DANIEL M.
<u>60029491</u>	Not Issued	159	10/25/1996	PROCESS FOR MANUFACTURE OF MOS GATED DEVICE WITH SELF ALIGNED CELLS	KINZER , DANIEL M.
<u>09432210</u>	<u>6144065</u>	150	11/03/1999	MOS GATED DEVICE WITH SELF ALIGNED CELLS	KINZER , DANIEL M.
<u>09161790</u>	<u>6133632</u>	150	09/28/1998	COMMONLY HOUSED DIVERSE SEMICONDUCTOR DEVICE	KINZER , DANIEL M.
<u>08618350</u>	<u>5844259</u>	150	03/19/1996	VERTICAL CONDUCTION MOS CONTROLLED THYRISTOR WITH INCREASED IGBT AREA AND CURRENT LIMITING	KINZER , DANIEL M.
<u>08308739</u>	Not Issued	166	09/19/1994	SURFACE MOUNT PACKAGE WITH IMPROVED HEAT TRANSFER	KINZER , DANIEL M.
<u>08308655</u>	Not Issued	166	09/19/1994	HIGH SPEED IGBT	KINZER , DANIEL M.
<u>08308556</u>	<u>5548133</u>	150	09/19/1994	IGBT WITH INCREASED RUGGEDNESS	KINZER , DANIEL M.
<u>07474625</u>	<u>4996577</u>	150	01/29/1990	PHOTOVOLTAIC ISOLATOR AND PROCESS OF MANUFACTURE THEREOF	KINZER , DANIEL M.
<u>06451795</u>	Not Issued	166	12/21/1982	STRUCTURE AND METHOD OF MANUFACTURE OF HIGH POWER MOSFET DEVICE	KINZER , DANIEL M.

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Day : Sunday
 Date: 7/11/2004
 Time: 18:54:17

Inventor Name Search Result

Your Search was:

Last Name = QU

First Name = ZHIJUN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 11
<u>60442316</u>	Not Issued	020	01/22/2003	SUPERJUNCTION DEVICE AND PROCESS FOR ITS MANUFACTURE	QU, ZHIJUN
<u>60417212</u>	Not Issued	020	10/08/2002	SUPERJUNCTION DEVICE WITH ADDED CHARGE AT TOP OF P PYLONS TO INCREASE RUGGEDNESS	QU, ZHIJUN
<u>60394038</u>	Not Issued	159	07/03/2002	TERMINATION STRUCTURE FOR MOSGATED POWER DEVICE	QU, ZHIJUN
<u>60394037</u>	Not Issued	159	07/03/2002	SUPERJUNCTION DEVICE AND PROCESS FOR ITS MANUFACTURE	QU, ZHIJUN
<u>60303724</u>	Not Issued	159	07/06/2001	TERMINATION STRUCTURE FOR SUPERJUNCTION DEVICE	QU, ZHIJUN
<u>10680898</u>	Not Issued	030	10/08/2003	SUPERJUNCTION DEVICE WITH ADDED CHARGE AT TOP OF PYLONS TO INCREASE RUGGEDNESS	QU, ZHIJUN
<u>10613586</u>	Not Issued	041	07/02/2003	TERMINATION STRUCTURE FOR MOSGATED POWER DEVICES	QU, ZHIJUN
<u>10613327</u>	Not Issued	030	07/03/2003	SUPERJUNCTION DEVICE AND PROCESS FOR ITS MANUFACTURE	QU, ZHIJUN
<u>10274644</u>	Not Issued	061	10/17/2002	DUAL EPITAXIAL LAYER FOR HIGH VOLTAGE VERTICAL CONDUCTION POWER MOSFET DEVICES	QU, ZHIJUN
<u>10190152</u>	<u>6621122</u>	150	07/03/2002	TERMINATION STRUCTURE FOR SUPERJUNCTION DEVICE	QU, ZHIJUN
<u>09329156</u>	Not Issued	124	06/09/1999	DUAL EPITAXIAL LAYER	QU, ZHIJUN

				FOR HIGH VOLTAGE VERTICAL CONDUCTION POWER MOSFET DEVICES	
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Inventor Search Completed: No Records to Display.

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Inventor		<input type="button" value="Search"/>

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	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	112	SUPERJUNCTION	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:46
2	BRS	78	SUPERJUNCTION and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:47
3	BRS	5	SUPERJUNCTION and epitaxial and pedestals	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:49
4	BRS	2	SUPERJUNCTION and epitaxial and (implant\$5 same heat\$3 same diffuse)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:49
5	BRS	59	SUPERJUNCTION and epitaxial same implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 18:55
6	BRS	52	SUPERJUNCTION and epitaxial same implant\$5 and (expand\$3 or diffus\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:53
7	BRS	6	SUPERJUNCTION and epitaxial same implant\$5 and ((expand\$3 or diffus\$3) same heat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:53
8	BRS	1	"09/693574"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/09 19:55
9	BRS	7	438/136.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
10	BRS	455	438/140.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
11	BRS	223	438/172.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
12	BRS	98	438/186.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
13	BRS	85	438/192.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
14	BRS	53	438/194.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
15	BRS	87	438/195.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
16	BRS	189	438/212.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03
17	BRS	561	438/268.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:03

	Type	Hits	Search Text	DBs	Time Stamp
18	BRS	21369	epitaxial with silicon and (wafer or substrate) with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:05
19	BRS	17	SUPERJUNCTION and epitaxial same implant\$5 and epitaxial with silicon and (wafer or substrate) with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:05
20	BRS	19	SUPERJUNCTION and epitaxial with silicon and (wafer or substrate) with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:11
21	BRS	11759	epitaxial near3 silicon and (wafer or substrate) near3 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:11
22	BRS	4642	epitaxial near3 silicon and (wafer or substrate) near3 silicon and junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:12
23	BRS	14	epitaxial near3 silicon and (wafer or substrate) near3 silicon and superjunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:12
24	BRS	145	first near3 epitaxial near3 silicon and (wafer or substrate) near3 silicon and junction and second near3 epitaxial near3 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:13
25	BRS	58	first near3 epitaxial near3 silicon and (wafer or substrate) near3 silicon and junction and second near3 epitaxial near3 silicon and epitaxial with (implanting or implant or implanted)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:14
26	BRS	71	first near3 epitaxial near3 silicon and (wafer or substrate) near3 silicon and junction and second near3 epitaxial near3 silicon and epitaxial with (implanting or implant or implanted or implantation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/11 19:14